DOCUMENT CHANGE REQUEST

DCR number 1278	Changes required for: General	Originator: Steve Thacker	
Date: 2019/09/06	Date sent: 2019/06/12	Organisation: ESCC Executive Secretariat	
Status: IMPLEMENTED			

Title:	TRANSISTORS, POWER, MOSFET, N-CHANNEL,		
Number:	5205/030	Issue:	1

Other documents affected:

Page:

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Paragraph:

1.5 Note 1

Original wording:

As per 5205/030 issue 1

Proposed wording:

Safe Operating area figure for Variant 03 is amended; see attached mark-up specification 5205/030 Draft 2A for details.

Note: several additional minor editorial changes are included including the addition of ESCC reference spec hyperlinks and internal paragraph cross-references.

Justification:

This DCR is raised at the request of supporting ESCCQPL Manufacturer Infineon who have stated the following in justification:
1. We noticed that the RDSon limit-line has been calculated with the RDSon value at room temperature, instead of the one at Tj(max). We would like to correct this.

2. The DC and 10ms curves are slightly overrated, therefore the SOA screening test conditions are too tight. We would like to relax the test conditions and decrease the SOA.

Attachments:
escc5205030iss2_done.docx
Modifications:
N/A
Approval signature:

Date signed:
2019-09-06